

IN THE CLAIMS

1-12. (*Canceled*)

13. (*Currently Amended*) A method for megasonic cleaning of
semiconductor wafers comprising the steps of:
generating two or more parallel sets of megasonic waves in a cleaning
fluid;
5 immersing semiconductors in the cleaning fluid;
moving the wafers in the cleaning fluid ~~along a path~~ through said
megasonic waves and transverse to the megasonic waves ~~and traversing said~~
~~path two or more times.~~

14. (*Original*) The method of claim 13 wherein the megasonic waves
are generated across parallel regions of the fluid and the step of moving the
wafers comprises reciprocating the wafers through said parallel regions.

15. (*Currently Amended*) A method for megasonic cleaning of
semiconductor wafers comprising the steps of:
generating megasonic waves with a laminar ~~energy wave front~~ flow in a
cleaning fluid in a container; and

- 5 intercepting the generated waves inside the container and dispersing
the waves in a divergent manner; and
exposing the semiconductor wafers to the dispersed megasonic waves
within the cleaning fluid.

16-26. (Canceled)